

## Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}$                            | $I_D$<br>$T_A = +25^\circ\text{C}$ |
|---------------|---|------------------------------------|
| -60V          | 125m $\Omega$ @ $V_{GS} = -10\text{V}$  | -4.3A                              |
|               | 190m $\Omega$ @ $V_{GS} = -4.5\text{V}$ | -3.5A                              |

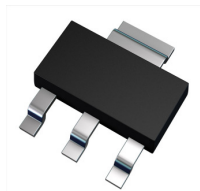
## Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

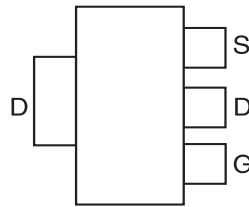
## Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

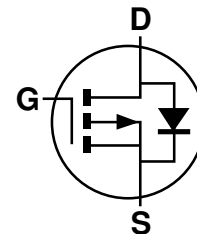
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

## Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.112 grams (Approximate)

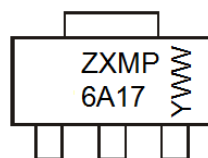
## Ordering Information (Notes 4 & 5)

| Part Number  | Compliance | Case   | Packaging           |
|--------------|------------|--------|---------------------|
| ZXMP6A17GQTA | Automotive | SOT223 | 1,000 / Tape & Reel |

- Note:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information

SOT223



ZXMP6A17 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: 5 = 2015)  
 WW or  $\bar{W}\bar{W}$  = Week (01 - 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

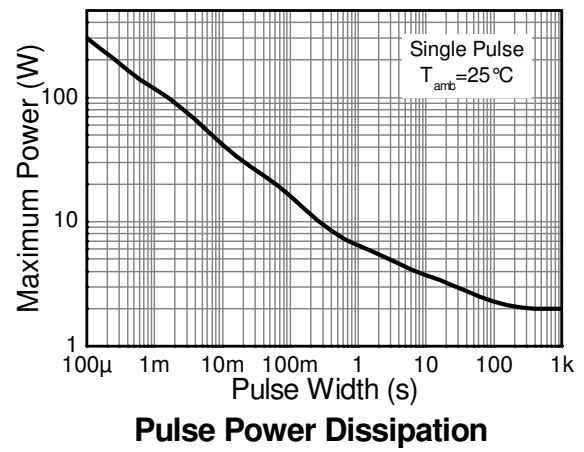
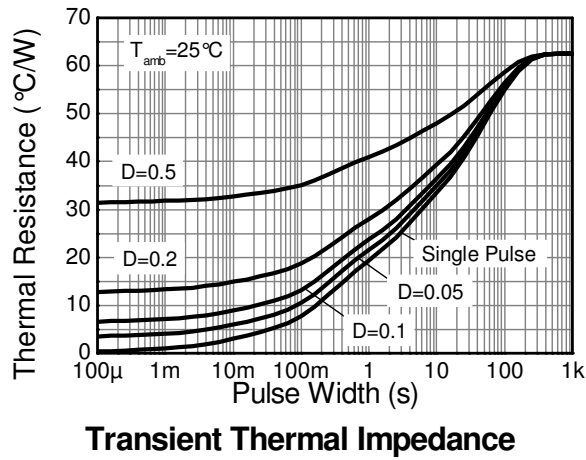
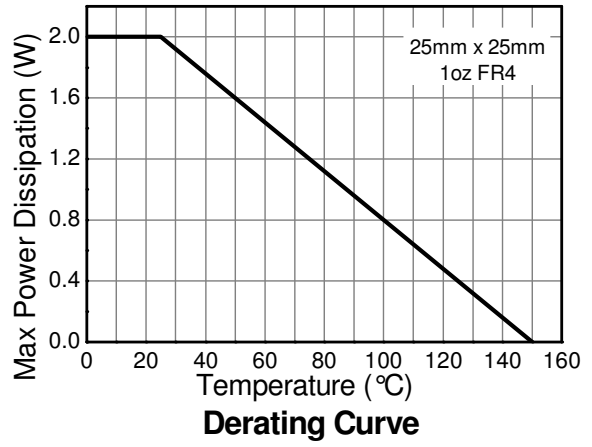
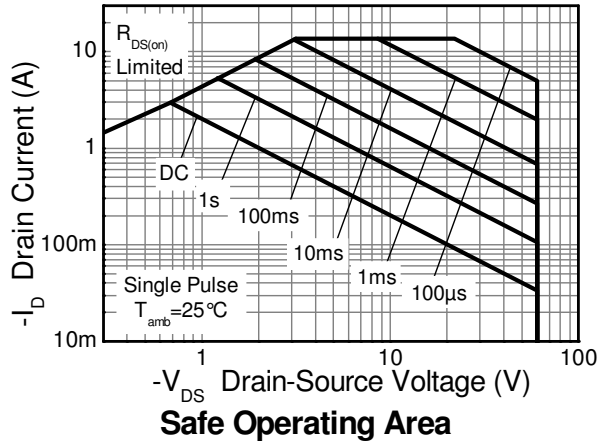
| Characteristic                         |                       |                                    | Symbol    | Value    | Unit  |   |
|--|-----------------------|------------------------------------|-----------|----------|-------|---|
| Drain-Source Voltage                   |                       |                                    | $V_{DSS}$ | -60      | V     |   |
| Gate-Source Voltage                    |                       |                                    | $V_{GS}$  | $\pm 20$ | V     |   |
| Continuous Drain Current               | $V_{GS} = 10\text{V}$ | (Note 7)                           | $I_D$     | -4.3     | A     |   |
|  |                       | $T_A = +70^\circ\text{C}$ (Note 7) |           | -3.5     |       |   |
|  |                       | (Note 6)                           |           | -3       |       |   |
| Pulsed Drain Current                   | $V_{GS} = 10\text{V}$ | (Note 8)                           | $I_{DM}$  | -13.7    | A     |   |
| Continuous Source Current (Body Diode) |                       |                                    | (Note 7)  | $I_S$    | -4.8  | A |
| Pulsed Source Current (Body Diode)     |                       |                                    | (Note 8)  | $I_{SM}$ | -13.7 | A |

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                          |                        | Symbol          | Value       | Unit                      |
|---|------------------------|-----------------|-------------|---------------------------|
| Power Dissipation                       | (Note 6)               | $P_D$           | 2           | W                         |
|   | Linear Derating Factor |                 | 16          |                           |
|   | (Note 7)               |                 | 3.9         | mW/ $^\circ\text{C}$      |
|   |                        |                 | 31          |                           |
| Thermal Resistance, Junction to Ambient | (Note 6)               | $R_{\theta JA}$ | 62.5        | $^\circ\text{C}/\text{W}$ |
|   | (Note 7)               |                 | 32          |                           |
| Thermal Resistance, Junction to Lead    | (Note 9)               | $R_{\theta JL}$ | 9.8         |                           |
| Operating and Storage Temperature Range |                        | $T_J, T_{STG}$  | -55 to +150 | $^\circ\text{C}$          |

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  7. Same as Note 6, except the device is measured at  $t \leq 10\text{sec}$ .
  8. Same as Note 6, except the device is pulsed with  $D = 0.02$  and pulse width 300 $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  9. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

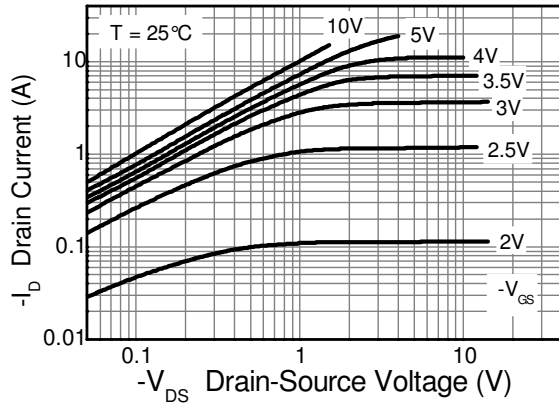


**Electrical Characteristics** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

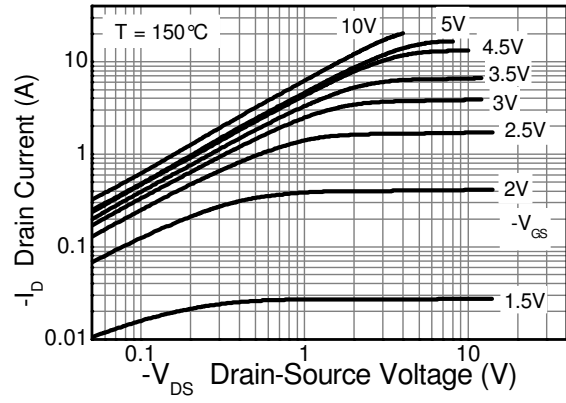
| Characteristic                              | Symbol              | Min | Typ   | Max   | Unit | Test Condition  |
|---|---------------------|-----|-------|-------|------|---|
| <b>OFF CHARACTERISTICS</b>                  |                     |     |       |       |      |   |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>   | -60 | —     | —     | V    | I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V   |
| Zero Gate Voltage Drain Current             | I <sub>DSS</sub>    | —   | —     | -0.5  | μA   | V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                         | I <sub>GSS</sub>    | —   | —     | ±100  | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V  |
| <b>ON CHARACTERISTICS</b>                   |                     |     |       |       |      |   |
| Gate Threshold Voltage                      | V <sub>GS(th)</sub> | -1  | —     | —     | V    | I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>                                  |
| Static Drain-Source On-Resistance (Note 10) | R <sub>DS(on)</sub> | —   | 0.096 | 0.125 | Ω    | V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.2A  |
|   |                     |     | 0.12  | 0.19  |      | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.8A   |
| Forward Transconductance (Notes 10 & 11)    | g <sub>fs</sub>     | —   | 4.7   | —     | S    | V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.2A  |
| Diode Forward Voltage (Note 10)             | V <sub>SD</sub>     | —   | -0.85 | -0.95 | V    | I <sub>S</sub> = -2A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25 °C                         |
| Reverse Recovery Time (Note 11)             | t <sub>rr</sub>     | —   | 25.1  | —     | ns   | I <sub>S</sub> = -1.7A, di/dt = 100A/μs,  |
| Reverse Recovery Charge (Note 11)           | Q <sub>rr</sub>     | —   | 27.2  | —     | nC   | T <sub>J</sub> = +25 °C   |
| <b>DYNAMIC CHARACTERISTICS (Note 11)</b>    |                     |     |       |       |      |   |
| Input Capacitance                           | C <sub>iss</sub>    | —   | 637   | —     | pF   | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V<br>f = 1MHz                                    |
| Output Capacitance                          | C <sub>oss</sub>    | —   | 70    | —     | pF   |   |
| Reverse Transfer Capacitance                | C <sub>rss</sub>    | —   | 53    | —     | pF   |   |
| Total Gate Charge (Note 12)                 | Q <sub>g</sub>      | —   | 9     | —     | nC   | V <sub>GS</sub> = -4.5V   |
| Total Gate Charge (Note 12)                 | Q <sub>g</sub>      | —   | 17.7  | —     | nC   | V <sub>GS</sub> = -10V<br>V <sub>DS</sub> = -30V<br>I <sub>D</sub> = -2.2A                  |
| Gate-Source Charge (Note 12)                | Q <sub>gs</sub>     | —   | 1.6   | —     | nC   |   |
| Gate-Drain Charge (Note 12)                 | Q <sub>gd</sub>     | —   | 4.4   | —     | nC   |   |
| Turn-On Delay Time (Note 12)                | t <sub>D(on)</sub>  | —   | 2.6   | —     | ns   | V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V<br>I <sub>D</sub> = -1A, R <sub>G</sub> ≅ 6Ω |
| Turn-On Rise Time (Note 12)                 | t <sub>r</sub>      | —   | 3.4   | —     | ns   |   |
| Turn-Off Delay Time (Note 12)               | t <sub>D(off)</sub> | —   | 26.2  | —     | ns   |   |
| Turn-Off Fall Time (Note 12)                | t <sub>f</sub>      | —   | 11.3  | —     | ns   |   |

- Notes:
10. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
  11. For design aid only, not subject to production testing.
  12. Switching characteristics are independent of operating junction temperatures.

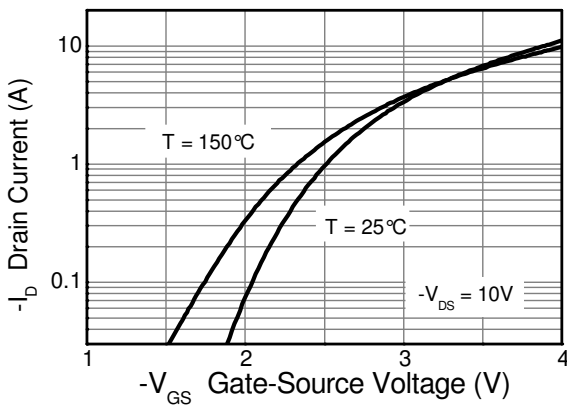
**Typical Characteristics**



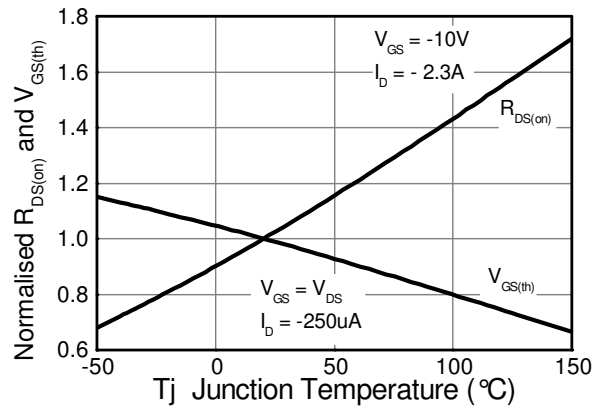
**Output Characteristics**



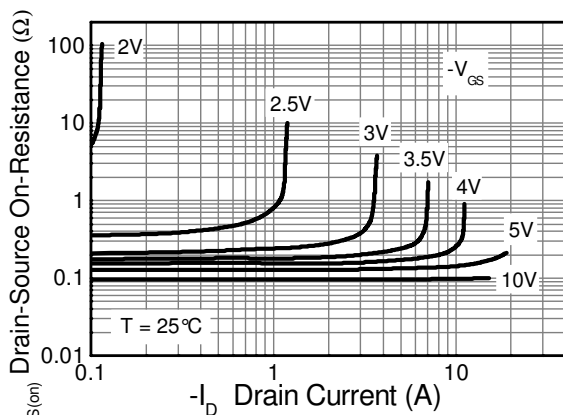
**Output Characteristics**



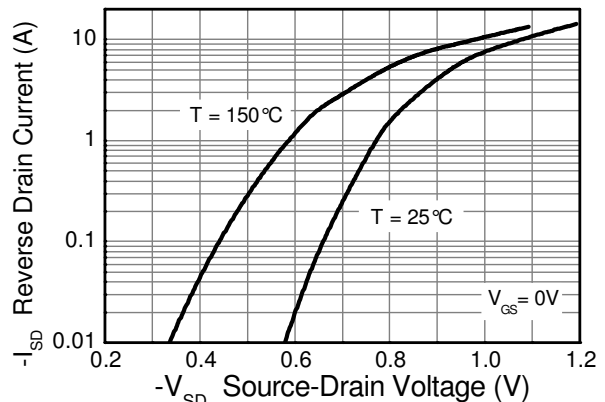
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

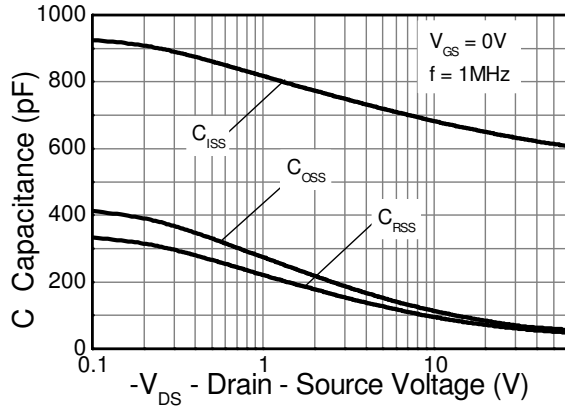


**On-Resistance v Drain Current**

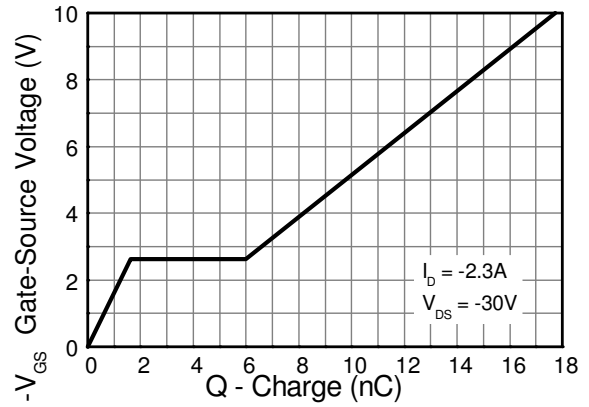


**Source-Drain Diode Forward Voltage**

**Typical Characteristics** (continued)

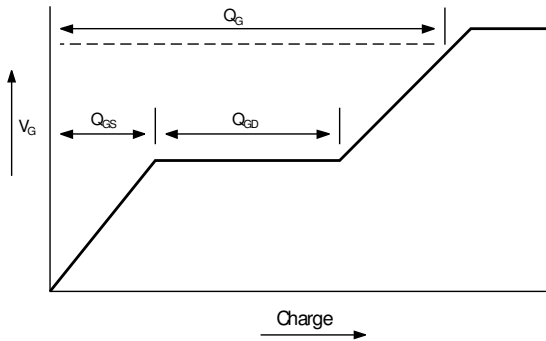


**Capacitance v Drain-Source Voltage**

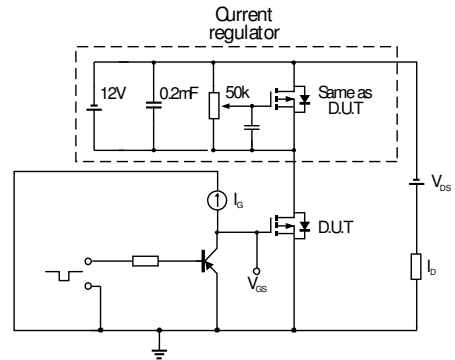


**Gate-Source Voltage v Gate Charge**

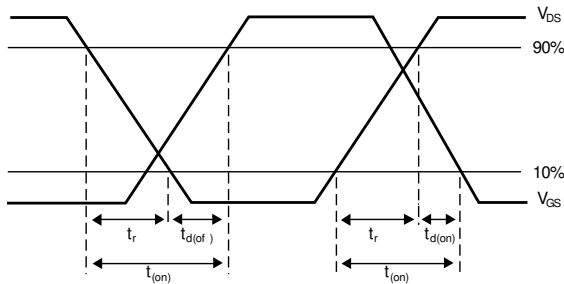
**Test Circuits**



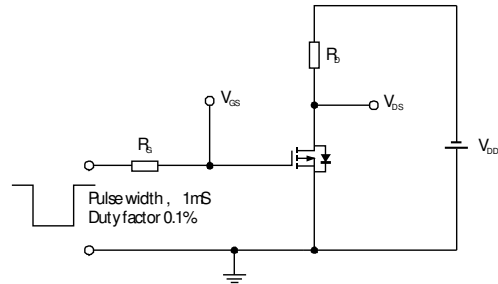
**Basic gate charge waveform**



**Gate charge test circuit**



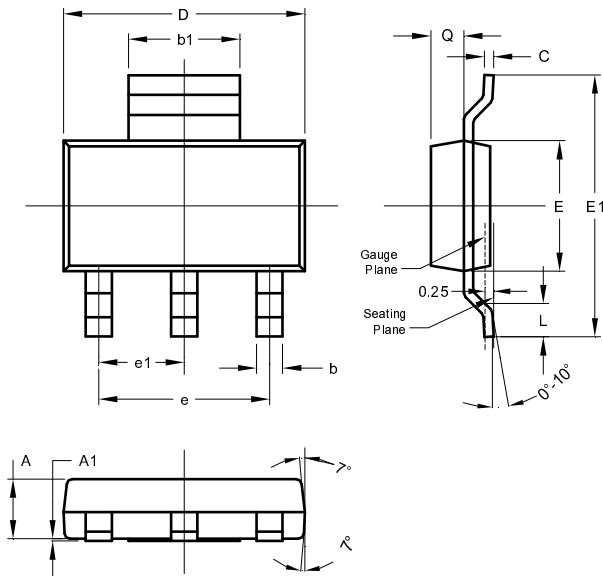
**Switching time waveforms**



**Switching time test circuit**

**Package Outline Dimensions**

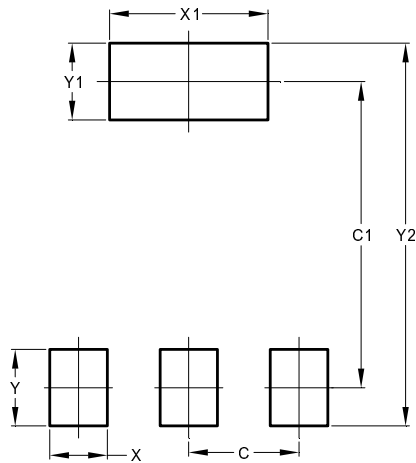
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| SOT223               |       |      |      |
|----------------------|-------|------|------|
| Dim                  | Min   | Max  | Typ  |
| A                    | 1.55  | 1.65 | 1.60 |
| A1                   | 0.010 | 0.15 | 0.05 |
| b                    | 0.60  | 0.80 | 0.70 |
| b1                   | 2.90  | 3.10 | 3.00 |
| C                    | 0.20  | 0.30 | 0.25 |
| D                    | 6.45  | 6.55 | 6.50 |
| E                    | 3.45  | 3.55 | 3.50 |
| E1                   | 6.90  | 7.10 | 7.00 |
| e                    | -     | -    | 4.60 |
| e1                   | -     | -    | 2.30 |
| L                    | 0.85  | 1.05 | 0.95 |
| Q                    | 0.84  | 0.94 | 0.89 |
| All Dimensions in mm |       |      |      |

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 2.30          |
| C1         | 6.40          |
| X          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |

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